



Product Specifications

PART NO.:

VL41D1G63B-K0/K9/F8S

REV: 1.0

General Information

8GB 1Gx72 DDR3 SDRAM LOW VOLTAGE ECC UNBUFFERED SO-UDIMM 204-PIN

Description

The VL41D1G63B is a 1Gx72 DDR3 SDRAM high density SO-UDIMM. This dual rank memory module consists of eighteen CMOS 512Mx8 bits with 8 banks DDR3 synchronous DRAMs in BGA packages and a 2K EEPROM in an 8-pin MLF package. This module is a 204-pin small-outline dual in-line memory module and is intended for mounting into an edge connector socket. Decoupling capacitors are mounted on the printed circuit board for each DDR3 SDRAM.

Features

- 204-pin, unbuffered small-outline dual in-line memory module (SO-UDIMM)
- Supports ECC error detection and correction
- Fast data transfer rates: PC3-12800, PC3-10600, PC3-8500
- VDD = VDDQ = 1.35V (1.28V~1.45V) & 1.5V (1.425V~1.575V)
- JEDEC standard 1.35V (1.28V~1.45V) & 1.5V (1.425V~1.575V)
- VDDSPD = 3.0V to 3.6V
- Eight internal component banks for concurrent operation
- 8-bit pre-fetch architecture
- Bi-directional differential data-strobe
- Nominal and dynamic on-die termination (ODT)
- ZQ calibration support
- Programmable CAS# latency:
11 (DDR3-1600), 9 (DDR3-1333), 7 (DDR3-1066)
- Programmable burst length (8)
- Average refresh period 7.8 us
- Asynchronous reset
- Fly-by topology
- On board terminated command, address, and control bus
- Serial presence detect (SPD) EEPROM with thermal sensor
- Thermal sensor range: -40°C to +125°C (Max +/-3°C accuracy)
- Lead-free, RoHS compliant
- Gold edge contacts
- PCB: Height 30.00mm (1.181"), double sided component
- Operating temperature (TOPER): - Commercial (0°C ≤ Tc ≤ 95°C)
- Industrial (-40°C ≤ Tc ≤ 95°C)

Notes: Double refresh rate is required when 85°C < TOPER ≤ 95°C.
TOPER is DRAM case temperature (Tc).

Pin Description

Pin Name	Function
A0~A15	Address Inputs
A10/AP	Address Input/ Autoprecharge
A12/BC#	Address Input/ Burst Chop
BA0~BA2	Bank Address Inputs
DQ0~DQ63	Data Input/Output
DQS0~DQS8	Data Strobes
DQS0#~DQS8#	Data Strobes Complement
DM0~DM8	Data Masks
CB0~CB7	Data Check Bits I/O
CK0,CK0#, CK1,CK1#	Clock Input
ODT0, ODT1	On-die Termination Control
CKE0, CKE1	Clock Enables
CS0#, CS1#	Chip Selects
RAS#	Row Address Strobes
CAS#	Column Address Strobes
WE#	Write Enable
VDD	Voltage Supply
VSS	Ground
SA0~SA1	SPD Address
SDA	SPD Data Input/Output
SCL	SPD Clock Input
EVENT#	Temperature Event Output
VREFCA	Reference Voltage for CA
VREFDQ	Reference Voltage for DQ
VDDSPD	SPD Voltage Supply
VTT	Termination Voltage
RESET#	Register and SDRAM Control
NC	No Connect

Order Information:

VL41D1G63B-K0 S X-X

OPERATING TEMPERATURE

None: Commercial
S1: Industrial screening

DRAM DIE
(Option)

DRAM MANUFACTURER
S - SAMSUNG

MODULE SPEED

K0: PC3-12800 @ CL11
K9: PC3-10600 @ CL9
F8: PC3-8500 @ CL7

VL: Lead-free/RoHS



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Pin Configuration

204-PIN DDR3 SO-UDIMM FRONT

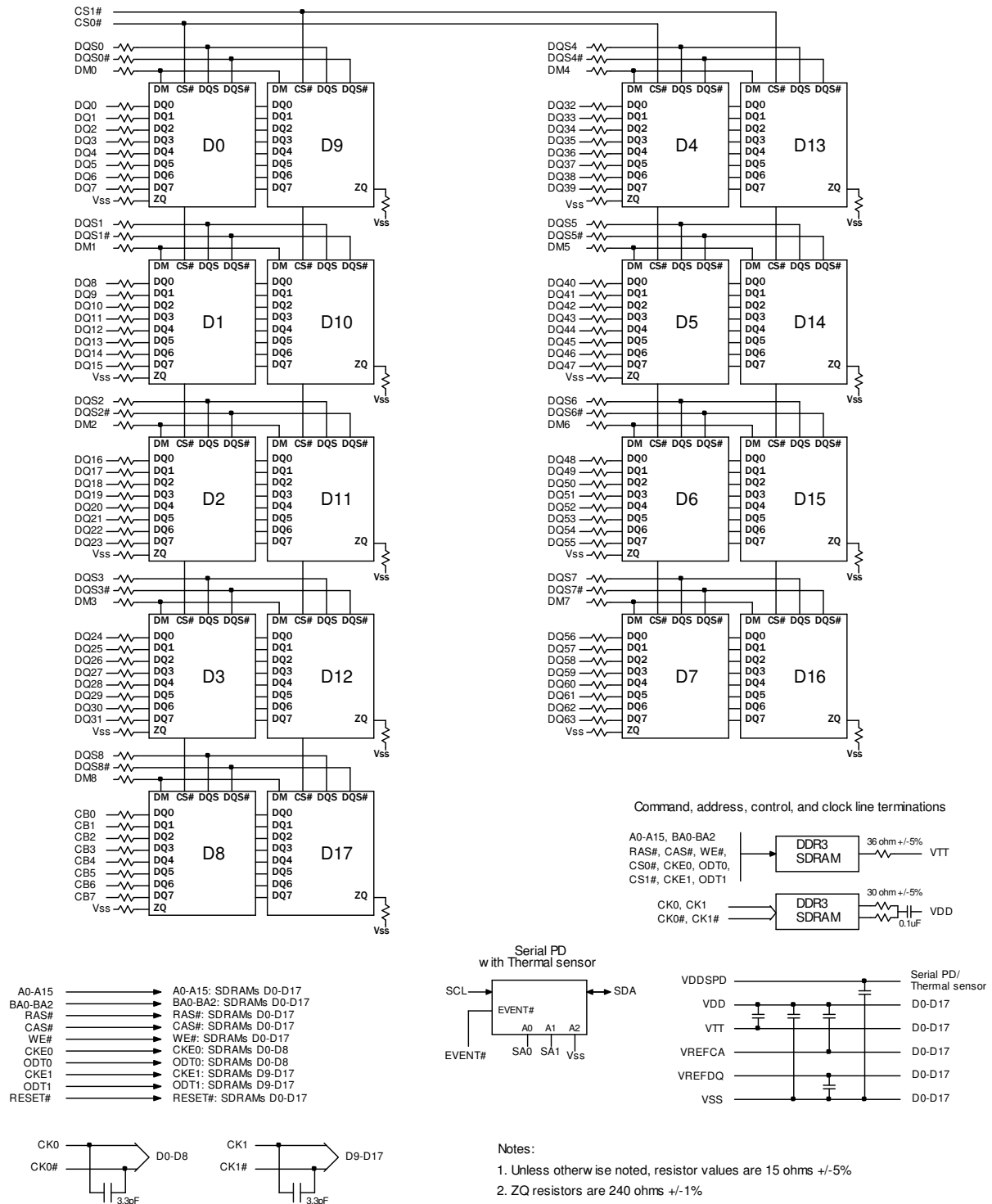
Pin	Name	Pin	Name	Pin	Name	Pin	Name
1	VREFDQ	53	VSS	105	A1	157	DM5
3	VSS	55	DQ24	107	A0	159	DQ42
5	DQ0	57	DQ25	109	VDD	161	DQ43
7	DQ1	59	DM3	111	CK0	163	VSS
9	VSS	61	VSS	113	CK0#	165	DQ48
11	DM0	63	DQ26	115	VDD	167	DQ49
13	DQ2	65	DQ27	117	A10/AP	169	VSS
15	DQ3	67	VSS	119	BA0	171	DQS6#
17	VSS	69	CB0	121	WE#	173	DQS6
19	DQ8	71	CB1	123	VDD	175	VSS
21	DQ9	73	VSS	125	CAS#	177	DQ50
23	VSS	75	DQS8#	127	CS0#	179	DQ51
25	DQS1#	77	DQS8	129	CS1#	181	VSS
27	DQS1	79	VSS	131	VDD	183	DQ56
29	VSS	81	CB2	133	DQ32	185	DQ57
31	DQ10	83	CB3	135	DQ33	187	VSS
33	DQ11	85	VDD	137	VSS	189	DM7
35	VSS	87	CKE0	139	DQS4#	191	DQ58
37	DQ16	89	CKE1	141	DQS4	193	DQ59
39	DQ17	91	BA2	143	VSS	195	VSS
41	VSS	93	VDD	145	DQ34	197	SA0
43	DQS2#	95	A12/BC#	147	DQ35	199	VDDSPD
45	DQS2	97	A8	149	VSS	201	SA1
47	VSS	99	A5	151	DQ40	203	VTT
49	DQ18	101	VDD	153	DQ41		
51	DQ19	103	A3	155	VSS		

204-PIN DDR3 SO-UDIMM BACK

Pin	Name	Pin	Name	Pin	Name	Pin	Name
2	VSS	54	DQ28	106	A2	158	VSS
4	DQ4	56	DQ29	108	BA1	160	DQ46
6	DQ5	58	VSS	110	VDD	162	DQ47
8	VSS	60	DQS3#	112	CK1	164	VSS
10	DQS0#	62	DQS3	114	CK1#	166	DQ52
12	DQS0	64	VSS	116	VDD	168	DQ53
14	VSS	66	DQ30	118	CS3# *	170	VSS
16	DQ6	68	DQ31	120	CS2# *	172	DM6
18	DQ7	70	VSS	122	RAS#	174	DQ54
20	VSS	72	CB4	124	VDD	176	DQ55
22	DQ12	74	CB5	126	ODT0	178	VSS
24	DQ13	76	DM8	128	ODT1	180	DQ60
26	VSS	78	VSS	130	A13	182	DQ61
28	DM1	80	CB6	132	VDD	184	VSS
30	RESET#	82	CB7	134	DQ36	186	DQS7#
32	VSS	84	VREFCA	136	DQ37	188	DQS7
34	DQ14	86	VDD	138	VSS	190	VSS
36	DQ15	88	A15	140	DM4	192	DQ62
38	VSS	90	A14	142	DQ38	194	DQ63
40	DQ20	92	A9	144	DQ39	196	VSS
42	DQ21	94	VDD	146	VSS	198	EVENT#
44	DM2	96	A11	148	DQ44	200	SDA
46	VSS	98	A7	150	DQ45	202	SCL
48	DQ22	100	A6	152	VSS	204	VTT
50	DQ23	102	VDD	154	DQS5#		
52	VSS	104	A4	156	DQS5		

*: These pins are not used in this module.

Function Block Diagram





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Absolute Maximum Ratings

Symbol	Parameter		Min	Max	Unit
VDD	Voltage on VDD pin relative to VSS		-0.4	1.975	V
VDDQ	Voltage on VDDQ pin relative to VSS		-0.4	1.975	V
VIN, VOUT	Voltage on any pin relative to VSS		-0.4	1.975	V
TSTG	Storage temperature		-55	100	°C
IL	Input leakage current; Any input 0V<VIN<VDD; VREF input 0V<VIN<0.95V; Other pins not under test = 0V	Address, RAS#, CAS#, WE#, BA	-36	36	uA
		CS#, CKE, ODT, CK, CK#	-18	18	uA
		DM	-4	4	uA
IOZ	Output leakage current; 0V<VOUT<VDDQ; DQs and ODT are disabled	DQ, DQS, DQS#	-10	10	uA
IVREF	VREF supply leakage current; VREF = Valid VREF level		-18	18	uA

DC Operating Conditions

Symbol	Parameter	Operating Voltage	Min	Typical	Max	Unit	Notes
VDD	Supply Voltage	1.35V	1.283	1.35	1.45	V	1,2
		1.5V	1.425	1.5	1.575		
VDDQ	I/O Supply Voltage	1.35V	1.283	1.35	1.45	V	1,2
		1.5V	1.425	1.5	1.575		
VREFDQ (DC)	I/O reference voltage DQ bus		$0.49 \times V_{DD}$	$0.5 \times V_{DD}$	$0.51 \times V_{DD}$	V	3,4
VREFCA (DC)	Input reference voltage CMD/ADD bus		$0.49 \times V_{DD}$	$0.5 \times V_{DD}$	$0.51 \times V_{DD}$	V	3,4
VTT	Termination Reference Voltage		$-0.483 \times V_{DDQ}$	$0.5 \times V_{DDQ}$	$+0.517 \times V_{DDQ}$	V	5

Note:

- Under all conditions VDDQ must be less than or equal to VDD.
- VDDQ tracks with VDD. AC parameters are measured with VDD and VDDQ tied together.
- The AC peak noise on VREF may not allow VREF to deviate from VREF(DC) by more than $\pm 1\%$ VDD.
- For reference: approximate $V_{DD}/2 \pm 15mV$.
- VTT termination voltage in excess of stated limit will adversely affect the command and address signals' voltage margin and will reduce timing margins.

Operating Temperature Condition

Symbol	Parameter		Rating	Units	Notes
TOPER	Operating temperature	Commercial	0 to 95	°C	1,2
		Industrial	-40 to +95		

Notes:

- Operating temperature is the case surface temperature on the center/top side of the DRAM. For the measurement conditions, please refer to JEDEC JESD51-2.
- At -40 to $+85^{\circ}C$, operation temperature range, all DRAM specifications will be supported. The refresh rate is required to double when $85^{\circ}C < TOPER \leq 95^{\circ}C$.



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Input DC Logic Level

All voltages referenced to VSS

Symbol	Parameter	Min	Max	Unit
1.35V				
Command and Address				
VIHCA(DC)	Input High (Logic 1) Voltage (DDR3-1066/1333/1600)	VREF + 0.090	VDD	V
VILCA(DC)	Input Low (Logic 0) Voltage (DDR3-1066/1333/1600)	VSS	VREF - 0.090	V
DQ and DM				
VIHDQ(DC)	Input High (Logic 1) Voltage (DDR3-1066/1333/1600)	VREF + 0.090	VDD	V
VILDQ(DC)	Input Low (Logic 0) Voltage (DDR3-1066/1333/1600)	VSS	VREF - 0.090	V
1.5V				
Command and Address				
VIHCA(DC)	Input High (Logic 1) Voltage (DDR3-1066/1333/1600)	VREF + 0.100	VDD	V
VILCA(DC)	Input Low (Logic 0) Voltage (DDR3-1066/1333/1600)	VSS	VREF - 0.100	V
DQ and DM				
VIHDQ(DC)	Input High (Logic 1) Voltage (DDR3-1066/1333/1600)	VREF + 0.100	VDD	V
VILDQ(DC)	Input Low (Logic 0) Voltage (DDR3-1066/1333/1600)	VSS	VREF - 0.100	V

Input AC Logic Level

All voltages referenced to VSS

Symbol	Parameter	Min	Max	Unit
1.35V				
Command and Address				
VIHCA(AC)	Input High (Logic 1) Voltage (DDR3-1066/1333/1600)	VREF + 0.160	-	V
VILCA(AC)	Input Low (Logic 0) Voltage (DDR3-1066/1333/1600)	-	VREF - 0.160	V
DQ and DM				
VIHDQ(AC)	Input High (Logic 1) Voltage (DDR3-1066)	VREF + 0.160	-	V
VILDQ(AC)	Input Low (Logic 0) Voltage (DDR3-1066)	-	VREF - 0.160	V
VIHDQ(AC)	Input High (Logic 1) Voltage (DDR3-1333/1600)	VREF + 0.135	-	V
VILDQ(AC)	Input Low (Logic 0) Voltage (DDR3-1333/1600)	-	VREF - 0.135	V
1.5V				
Command and Address				
VIHCA(AC)	Input High (Logic 1) Voltage (DDR3-1066/1333/1600)	VREF + 0.175	-	V
VILCA(AC)	Input Low (Logic 0) Voltage (DDR3-1066/1333/1600)	-	VREF - 0.175	V
DQ and DM				
VIHDQ(AC)	Input High (Logic 1) Voltage (DDR3-1066)	VREF + 0.175	-	V
VILDQ(AC)	Input Low (Logic 0) Voltage (DDR3-1066)	-	VREF - 0.175	V
VIHDQ(AC)	Input High (Logic 1) Voltage (DDR3-1333/1600)	VREF + 0.150	-	V
VILDQ(AC)	Input Low (Logic 0) Voltage (DDR3-1333/1600)	-	VREF - 0.150	V



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REV: 1.0

Input/Output Capacitance

TA=25°C, f=100MHz

Parameter	Symbol	K0 (DDR3-1600)		K9 (DDR3-1333)		F8 (DDR3-1066)		Unit
		Min	Max	Min	Max	Min	Max	
1.35V								
Input capacitance (A0~A15, BA0~BA2, RAS#, CAS#, WE#)	CIN1	17.5	27.4	17.5	27.4	17.5	27.4	pF
Input capacitance (CKE0, ODT0, CS0#)	CIN2	10.75	15.7	10.75	15.7	10.75	15.7	pF
Input capacitance (CK0, CK0#)	CIN3	11.2	16.6	11.2	16.6	11.2	18.4	pF
Input/Output capacitance (DQ, DQS, DQS#, CB, DM)	CIO	6.4	8.6	7	8.6	7	9	pF
1.5V								
Input capacitance (A0~A15, BA0~BA2, RAS#, CAS#, WE#)	CIN1	17.5	27.4	17.5	27.4	17.5	31	pF
Input capacitance (CKE0, ODT0, CS0#)	CIN2	10.75	15.7	10.75	15.7	10.75	17.5	pF
Input capacitance (CK0, CK0#)	CIN3	11.2	16.6	11.2	16.6	11.2	18.4	pF
Input/Output capacitance (DQ, DQS, DQS#, CB, DM)	CIO	6.8	8.6	7	9	7	9.4	pF



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IDD Specification

Condition	Symbol	K0 (DDR3-1600)		K9 (DDR3-1333)		F8 (DDR3-1066)		Unit
		1.35V	1.5V	1.35V	1.5V	1.35V	1.5V	
Operating one bank active-precharge current; tCK= tCK(IDD); tRC= tRC(IDD); tRAS= tRAS MIN(IDD); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING	IDD0*	540	540	495	495	495	495	mA
Operating one bank active-read-precharge current; IOUT = 0mA; BL = 8; CL = CL(IDD); AL = 0; tCK= tCK(IDD); tRC= tRC(IDD); tRAS= tRAS MIN(IDD); tRCD= tRCD(IDD); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as IDD4W.	IDD1*	630	630	585	585	585	585	mA
Precharge power-down current; All device banks idle; tCK= tCK(IDD); CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	IDD2P-F**	270	270	270	270	270	270	mA
	IDD2P-S**	270	270	270	270	270	270	mA
Precharge standby current; All device banks idle; tCK= tCK(IDD); CKE is HIGH; CS# is HIGH; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING.	IDD2N**	360	360	360	360	360	360	mA
Precharge quiet standby current; All device banks idle; tCK= tCK(IDD); CKE is HIGH; CS# is HIGH; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	IDD2Q**	360	360	360	360	360	360	mA
Active power-down current; All device banks open; tCK= tCK(IDD); CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING.	IDD3P**	360	360	360	360	270	360	mA
Active standby current; All device banks open; tCK= tCK(IDD); tRP= tRP(IDD); tRAS= tRAS MAX(IDD); CKE is HIGH, CS# is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING.	IDD3N**	540	540	540	540	450	540	mA
Operating burst read current; All device banks open; Continuous burst reads; IOUT = 0mA; BL = 8; CL = CL(IDD); AL = 0; tCK= tCK(IDD); tRAS= tRAS MAX(IDD); tRP= tRP(IDD); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as IDD4W.	IDD4R*	1035	1035	900	900	765	765	mA
Operating burst write current; All device banks open; Continuous burst writes; BL = 8; CL = CL(IDD); AL = 0; tCK= tCK(IDD); tRAS= tRAS MAX(IDD); tRP= tRP(IDD); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING.	IDD4W*	1080	1125	900	945	810	810	mA
Burst refresh current; tCK=tCK(IDD); Refresh command at every tRFC(IDD) interval; CKE is HIGH; CS# is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING.	IDD5**	2610	2610	2610	2610	2070	2160	mA
Self refresh current; CK and CK# at 0V; CKE < 0.2V; Other control and address bus inputs are FLOATING; Data bus inputs are FLOATING.	IDD6**	270	270	270	270	270	270	mA
Operating bank interleave read current; All bank interleaving reads; IOUT = 0mA; BL = 8; CL = CL(IDD); AL = tRCD(IDD) - 1*tCK(IDD); tCK= tCK(IDD); tRC= tRC(IDD); tRRD = tRRD(IDD); tRCD = 1*tCK(IDD); CKE is HIGH; CS# is HIGH between valid commands; Address bus inputs are STABLE during DESELECTs; Data pattern is same as IDD4R.	IDD7*	1665	1710	1620	1665	1305	1305	mA

Notes: IDD specification is based on Samsung B-die components.

*: Value calculated as one module rank in this operating condition, and all other module ranks in IDD2P (CKE LOW) mode.

** : Value calculated reflects all module ranks in this operating condition.



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REV: 1.0

AC TIMING PARAMETERS & SPECIFICATIONS

Parameter		Symbol	K0 (DDR3-1600)		K9 (DDR3-1333)		F8 (DDR3-1066)		Unit
			MIN	MAX	MIN	MAX	MIN	MAX	
Clock Timing									
Minimum Clock Cycle Time (DLL off mode)		tCK(DLL_OFF)	8	-	8	-	8	-	ns
Average Clock Period		tCK(avg)	1.25	<1.50	1.5	<1.875	1.875	<2.5	ns
Clock Period		tCK(abs)	tCK(avg)min + tJIT(per)min	tCK(avg)max + tJIT(per)max	tCK(avg)min + tJIT(per)min	tCK(avg)max + tJIT(per)max	tCK(avg)min + tJIT(per)min	tCK(avg)max + tJIT(per)max	ns
Average high pulse width		tCH(avg)	0.47	0.53	0.47	0.53	0.47	0.53	tCK(avg)
Average low pulse width		tCL(avg)	0.47	0.53	0.47	0.53	0.47	0.53	tCK(avg)
Clock Period Jitter		tJIT(per)	-70	70	-80	80	-90	90	ps
Clock Period Jitter during DLL locking period		tJIT(per, lck)	-60	60	-70	70	-80	80	ps
Cycle to Cycle Period Jitter		tJIT(cc)	140		160		180		ps
Cycle to Cycle Period Jitter during DLL locking period		tJIT(cc, lck)	120		140		160		ps
Cumulative error across 2 cycles		tERR(2per)	-103	103	-118	118	-132	132	ps
Cumulative error across 3 cycles		tERR(3per)	-122	122	-140	140	-157	157	ps
Cumulative error across 4 cycles		tERR(4per)	-136	136	-155	155	-175	175	ps
Cumulative error across 5 cycles		tERR(5per)	-147	147	-168	168	-188	188	ps
Cumulative error across 6 cycles		tERR(6per)	-155	155	-177	177	-200	200	ps
Cumulative error across 7 cycles		tERR(7per)	-163	163	-186	186	-209	209	ps
Cumulative error across 8 cycles		tERR(8per)	-169	169	-193	193	-217	217	ps
Cumulative error across 9 cycles		tERR(9per)	-175	175	-200	200	-224	224	ps
Cumulative error across 10 cycles		tERR(10per)	-180	180	-205	205	-231	231	ps
Cumulative error across 11 cycles		tERR(11per)	-184	184	-210	210	-237	237	ps
Cumulative error across 12 cycles		tERR(12per)	-188	188	-215	215	-242	242	ps
Cumulative error across n = 13, 14 ... 49, 50 cycles		tERR(nper)	tERR(nper)min =(1+ 0.68ln(n))*tJIT(per)min tERR(nper)max=(1+ 0.68ln(n))*tJIT(per)max						ps
Absolute clock HIGH pulse width		tCH(abs)	0.43	-	0.43	-	0.43	-	tCK(avg)
Absolute clock Low pulse width		tCL(abs)	0.43	-	0.43	-	0.43	-	tCK(avg)
Data Timing									
DQS,DQS# to DQ skew, per group, per access		tDQSQ	-	100	-	125	-	150	ps
DQ output hold time from DQS, DQS#		tQH	0.38	-	0.38	-	0.38	-	tCK(avg)
DQ low-impedance time from CK, CK#		tLZ(DQ)	-450	225	-500	250	-600	300	ps
DQ high-impedance time from CK, CK#		tHZ(DQ)	-	225	-	250	-	300	ps
Data setup time to DQS, DQS# referenced to Vih(ac)Vil(ac) levels	1.35V	tDS(base) (AC160)	-	-	-	-	40	-	ps
		tDS(base) (AC135)	25	-	45	-	-	-	
Data setup time to DQS, DQS# referenced to Vih(ac)Vil(ac) levels	1.5V	tDS(base) (AC175)	-	-	-	-	25	-	ps
		tDS(base) (AC150)	10	-	30	-	-	-	



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AC TIMING PARAMETERS & SPECIFICATIONS

Parameter	Symbol	K0 (DDR3-1600)		K9 (DDR3-1333)		F8 (DDR3-1066)		Unit
		MIN	MAX	MIN	MAX	MIN	MAX	
Data hold time to DQS, DQS# referenced to Vih(ac)/Vil(ac) levels	tDH(base)	55	-	75	-	110	-	ps
DQ and DM Input pulse width for each input	tDIPW	360	-	400	-	490	-	ps
Data Strobe Timing								
DQS, DQS# READ Preamble	tRPRE	0.9	-	0.9	-	0.9	-	tCK
DQS, DQS# differential READ Postamble	tRPST	0.3	-	0.3	-	0.3	-	tCK
DQS, DQS# output high time	tQSH	0.4	-	0.4	-	0.38	-	tCK(avg)
DQS, DQS# output low time	tQSL	0.4	-	0.4	-	0.38	-	tCK(avg)
DQS, DQS# WRITE Preamble	tWPRE	0.9	-	0.9	-	0.9	-	tCK
DQS, DQS# WRITE Postamble	tWPST	0.3	-	0.3	-	0.3	-	tCK
DQS, DQS# rising edge output access time from rising CK, CK#	tDQSCK	-225	225	-255	255	-300	300	ps
DQS, DQS# low-impedance time (Referenced from RL-1)	tLZ(DQS)	-450	225	-500	250	-600	300	ps
DQS, DQS# high-impedance time (Referenced from RL+BL/ 2)	tHZ(DQS)	-	225	-	250	-	300	ps
DQS, DQS# differential input low pulse width	tDQSL	0.45	0.55	0.45	0.55	0.45	0.55	tCK
DQS, DQS# differential input high pulse width	tDQSH	0.45	0.55	0.45	0.55	0.45	0.55	tCK
DQS, DQS# rising edge to CK, CK# rising edge	tDQSS	-0.27	0.27	-0.25	0.25	-0.25	0.25	tCK(avg)
DQS,DQS# falling edge setup time to CK, CK# rising edge	tDSS	0.18	-	0.2	-	0.2	-	tCK(avg)
DQS,DQS# falling edge hold time to CK, CK# rising edge	tDSH	0.18	-	0.2	-	0.2	-	tCK(avg)
Command and Address Timing								
DLL locking time	tDLLK	512	-	512	-	512	-	nCK
Internal READ Command to PRECHARGE Command delay	tRTP	max (4tCK,7.5ns)	-	max (4tCK,7.5ns)	-	max (4tCK,7.5ns)	-	
Delay from start of internal write transaction to internal read command	tWTR	max (4tCK,7.5ns)	-	max (4tCK,7.5ns)	-	max (4tCK,7.5ns)	-	
WRITE recovery time	tWR	15	-	15	-	15	-	ns
Mode Register Set command cycle time	tMRD	4	-	4	-	4	-	nCK
Mode Register Set command update delay	tMOD	max (12tCK,15ns)	-	max (12tCK,15ns)	-	max (12tCK,15ns)	-	
CAS# to CAS# command delay	tCCD	4	-	4	-	4	-	nCK
Auto precharge write recovery + precharge time	tDAL(min)	WR + roundup (tRP / tCK(AVG))						nCK
Multi-Purpose Register Recovery Time	tMPRR	1	-	1	-	1	-	nCK
ACTIVE to PRECHARGE command period	tRAS	35	9*tREFI	36	9*tREFI	37.5	9*tREFI	ns
ACTIVE to internal read or write delay time	tRCD	13.75	-	13.5	-	13.13	-	ns
PRECHARGE command period	tRP	13.75	-	13.5	-	13.13	-	ns
ACTIVE to ACTIVE or REF command period	tRC	48.75	-	49.5	-	50.63	-	ns
ACTIVE to ACTIVE command period for 1KB page size	tRRD	max (4tCK, 6ns)	-	max (4tCK, 6ns)	-	max (4tCK, 7.5ns)	-	
ACTIVE to ACTIVE command period for 2KB page size	tRRD	max (4tCK,7.5ns)	-	max (4tCK,7.5ns)	-	max (4tCK,10ns)	-	
Four activate window for 1KB page size	tFAW	30	-	30	-	37.5	-	ns
Four activate window for 2KB page size	tFAW	40	-	45	-	50	-	ns
Command and Address setup time to CK, CK# referenced to Vih(ac) / Vil(ac) levels	1.35V	tIS(base) (AC160)	-	-	-	140	-	ps
		tIS(base) (AC135)	185	-	205	-	-	



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AC TIMING PARAMETERS & SPECIFICATIONS

Parameter	Symbol	K0 (DDR3-1600)		K9 (DDR3-1333)		F8 (DDR3-1066)		Unit
		MIN	MAX	MIN	MAX	MIN	MAX	
Command and Address setup time to CK, CK# referenced to Vih(ac) / Vil(ac) levels	1.5V	tIS(base) (AC175)	-	-	-	125	-	ps
		tIS(base) (AC150)	170	-	190	-	-	
Command and Address hold time from CK, CK# referenced to Vih(ac) / Vil(ac) levels		tIH(base)	130	-	150	-	210	ps
Control & Address Input pulse width for each input		tIPW	560	-	620	-	780	ps
Refresh Timing								
4Gb REFRESH to REFRESH or REFRESH to ACTIVE command interval		tRFC	300	-	300	-	300	ns
Average periodic refresh interval (0 °C ≤ TCASE ≤ 85 °C)		tREFI	7.8	-	7.8	-	7.8	us
Average periodic refresh interval (85 °C ≤ TCASE ≤ 95 °C)		tREFI	3.9	-	3.9	-	3.9	us
Calibration Timing								
Power-up and RESET calibration time		tZQinitl	512	-	512	-	512	tCK
Normal operation Full calibration time		tZQoper	256	-	256	-	256	tCK
Normal operation Short calibration time		tZQCS	64	-	64	-	64	tCK
Reset Timing								
Exit Reset from CKE HIGH to a valid command		tXPR	max (5tCK, tRFC + 10ns)	-	max (5tCK, tRFC + 10ns)	-	max (5tCK, tRFC + 10ns)	-
Self Refresh Timing								
Exit Self Refresh to commands not requiring a locked DLL		tXS	max(5tC, tRFC+10ns)	-	max(5tC, tRFC+10ns)	-	max(5tC, tRFC + 10ns)	-
Exit Self Refresh to commands requiring a locked DLL		tXSDLL	tDLLK(min)	-	tDLLK(min)	-	tDLLK(min)	nCK
Minimum CKE low width for Self refresh entry to exit timing		tCKESR	tCKE(min) + 1tCK	-	tCKE(min) + 1tCK	-	tCKE(min) + 1tCK	-
Valid Clock Requirement after Self Refresh Entry (SRE)		tCKSRE	max(5tC, 10ns)	-	max(5tCK, 10ns)	-	max(5tCK, 10ns)	-
Valid Clock Requirement before Self Refresh Exit (SRX)		tCKSRX	max(5tC, 10ns)	-	max(5tCK, 10ns)	-	max(5tCK, 10ns)	-
Power Down Timing								
Exit Power Down with DLL to any valid command; Exit Precharge Power Down with DLL frozen to commands not requiring a locked DLL		tXP	max (3tCK, 6ns)	-	max (3tCK, 6ns)	-	max (3tCK, 7.5ns)	-
Exit Precharge Power Down with DLL frozen to commands requiring a locked DLL		tXPDLL	max (10tCK,24ns)	-	max (10tCK,24ns)	-	max (10tCK,24ns)	-
CKE minimum pulse width		tCKE	max (3tCK, 5ns)	-	max (3tCK, 5.625ns)	-	max (3tCK, 5.625ns)	-
Command pass disable delay		tCPDED	1	-	1	-	1	nCK
Power Down Entry to Exit Timing		tPD	tCKE(min)	9*tREFI	tCKE(min)	9*tREFI	tCKE(min)	9*tREFI
Timing of ACT command to Power Down entry		tACTPDEN	1	-	1	-	1	nCK
Timing of PRE command to Power Down entry		tPRPDEN	1	-	1	-	1	nCK
Timing of RD/RDA command to Power Down entry		tRDPDEN	RL + 4 + 1	-	RL + 4 + 1	-	RL + 4 + 1	-
Timing of WR command to Power Down entry BL8 (OTF, MRS), BL4OTF		tWRPDEN	WL + 4 + (tWR/ tCK(avg))	-	WL + 4 + (tWR/ tCK(avg))	-	WL + 4 + (tWR/ tCK(avg))	nCK
Timing of WRA command to Power Down entry BL8 (OTF, MRS), BL4OTF		tWRAPDEN	WL+4 +WR+1	-	WL+4 +WR+1	-	WL+4 +WR+1	nCK
Timing of WR command to Power Down entry (BL4MRS)		tWRPDEN	WL + 2 + (tWR/ tCK(avg))	-	WL + 2 + (tWR/ tCK(avg))	-	WL + 2 + (tWR/ tCK(avg))	nCK



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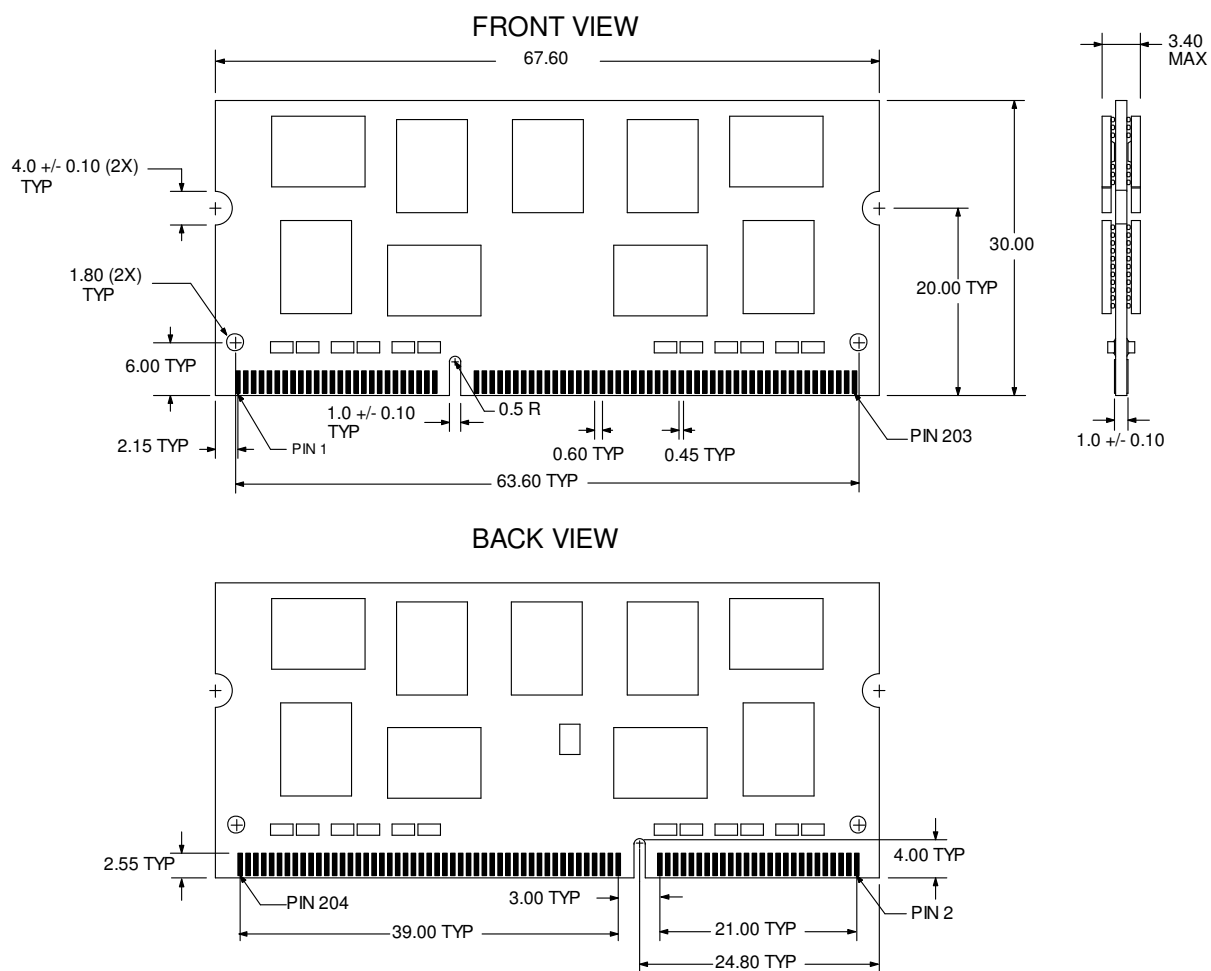
Parameter	Symbol	K0 (DDR3-1600)		K9 (DDR3-1333)		F8 (DDR3-1066)		Unit
		MIN	MAX	MIN	MAX	MIN	MAX	
Timing of WRA command to Power Down entry (BL4MRS)	tWRAPDEN	WL+2 +WR+1	-	WL+2 +WR+1	-	WL+2 +WR+1	-	nCK
Timing of REF command to Power Down entry	tREFPDEN	1	-	1	-	1	-	
Timing of MRS command to Power Down entry	tMRSPDEN	tMOD(min)	-	tMOD(min)	-	tMOD(min)	-	
ODT Timing								
ODT high time without write command or with write command and BC4	ODTH4	4	-	4	-	4	-	nCK
ODT high time with Write command and BL8	ODTH8	6	-	6	-	6	-	nCK
Asynchronous RTT turn-on delay (Power-Down with DLL frozen)	tAONPD	2	8.5	2	8.5	2	8.5	ns
Asynchronous RTT turn-off delay (Power-Down with DLL frozen)	tAOFPD	2	8.5	2	8.5	2	8.5	ns
ODT turn-on	tAON	-225	225	-250	250	-300	300	ps
RTT_NOM and RTT_WR turn-off time from ODTL off reference	tAOF	0.3	0.7	0.3	0.7	0.3	0.7	tCK(avg)
RTT dynamic change skew	tADC	0.3	0.7	0.3	0.7	0.3	0.7	tCK(avg)
Write Leveling Timing								
First DQS pulse rising edge after tDQSS margining mode is programmed	tWLMRD	40	-	40	-	40	-	tCK
DQS/DQS delay after tDQSS margining mode is programmed	tWLDQSEN	25	-	25	-	25	-	tCK
Setup time for tDQSS latch	tWLS	165	-	195	-	245	-	ps
Hold time for tDQSS latch	tWLH	165	-	195	-	245	-	ps
Write leveling output delay	tWLO	0	7.5	0	9	0	9	ns
Write leveling output error	tWLOE	0	2	0	2	0	2	ns

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Package Dimensions



Note: 1. All dimensions are in millimeters with tolerance $\pm$ 0.15mm unless otherwise specified.
 2. The dimensional diagram is for reference only.



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Revision History:

Date	Rev.	Page	Changes
05/22/2012	1.0	All	Spec released